



# BUK9Y19-100E

N-channel 100 V, 19 mΩ logic level MOSFET in LFPAK56

7 November 2016

Product data sheet

## 1. General description

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

## 2. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

## 3. Quick reference data

Table 1. Quick reference data

| Symbol                         | Parameter                        | Conditions   | Min | Typ  | Max | Unit |
|--------------------------------|----------------------------------|--|-----|------|-----|------|
| $V_{DS}$                       | drain-source voltage             | $25\text{ °C} \leq T_j \leq 175\text{ °C}$   | -   | -    | 100 | V    |
| $I_D$                          | drain current                    | $V_{GS} = 5\text{ V}; T_{mb} = 25\text{ °C};$ <a href="#">Fig. 2</a>   | -   | -    | 56  | A    |
| $P_{tot}$                      | total power dissipation          | $T_{mb} = 25\text{ °C};$ <a href="#">Fig. 1</a>  | -   | -    | 167 | W    |
| <b>Static characteristics</b>  |                                  |  |     |      |     |      |
| $R_{DSon}$                     | drain-source on-state resistance | $V_{GS} = 5\text{ V}; I_D = 15\text{ A}; T_j = 25\text{ °C};$ <a href="#">Fig. 11</a>  | -   | 14.6 | 19  | mΩ   |
| <b>Dynamic characteristics</b> |                                  |  |     |      |     |      |
| $Q_{GD}$                       | gate-drain charge                | $I_D = 15\text{ A}; V_{DS} = 80\text{ V}; V_{GS} = 5\text{ V};$<br>$T_j = 25\text{ °C};$ <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> | -   | 14.1 | -   | nC   |

## 4. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline   | Graphic symbol  |
|-----|--------|-----------------------------------|--|---|
| 1   | S      | source                            |  <p><b>LFAK56; Power-SO8 (SOT669)</b></p> |  |
| 2   | S      | source                            |  |   |
| 3   | S      | source                            |  |   |
| 4   | G      | gate                              |  |   |
| mb  | D      | mounting base; connected to drain |  |   |

## 5. Ordering information

Table 3. Ordering information

| Type number  | Package           |   |         |
|--------------|-------------------|---|---------|
|              | Name              | Description   | Version |
| BUK9Y19-100E | LFAK56; Power-SO8 | Plastic single-ended surface-mounted package (LFAK56; Power-SO8); 4 leads | SOT669  |

## 6. Marking

Table 4. Marking codes

| Type number  | Marking code |
|--------------|--------------|
| BUK9Y19-100E | 91910E       |

## 7. Limiting values

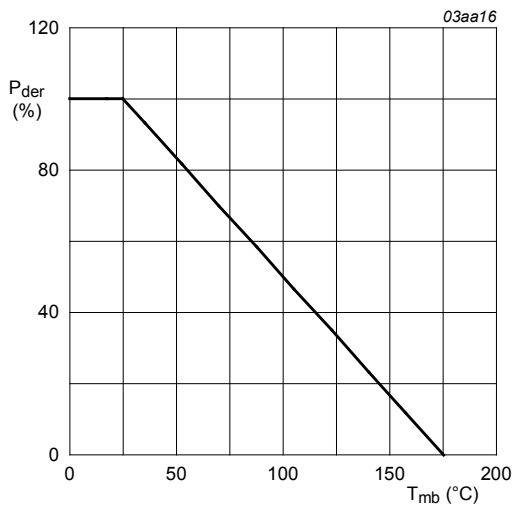
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter               | Conditions  | Min    | Max | Unit |
|-----------|-------------------------|---|--------|-----|------|
| $V_{DS}$  | drain-source voltage    | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                  | -      | 100 | V    |
| $V_{DGR}$ | drain-gate voltage      | $R_{GS} = 20\text{ k}\Omega$  | -      | 100 | V    |
| $V_{GS}$  | gate-source voltage     | DC; $T_j \leq 175\text{ °C}$  | -10    | 10  | V    |
|           |                         | Pulsed; $T_j \leq 175\text{ °C}$  | [1][2] | 15  | V    |
| $P_{tot}$ | total power dissipation | $T_{mb} = 25\text{ °C}$ ; Fig. 1  | -      | 167 | W    |
| $I_D$     | drain current           | $V_{GS} = 5\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 2                    | -      | 56  | A    |
|           |                         | $V_{GS} = 5\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; Fig. 2                   | -      | 40  | A    |
| $I_{DM}$  | peak drain current      | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 3 | -      | 226 | A    |

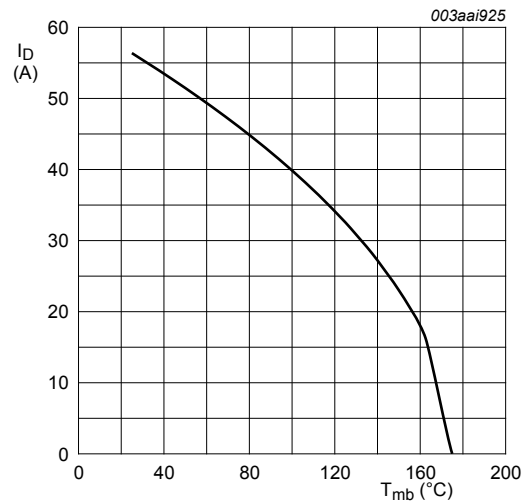
| Symbol                      | Parameter                                    | Conditions  | Min    | Max | Unit    |
|-----------------------------|--|---|--------|-----|---------|
| T <sub>stg</sub>            | storage temperature                          |   | -55    | 175 | °C      |
| T <sub>j</sub>              | junction temperature                         |   | -55    | 175 | °C      |
| <b>Source-drain diode</b>   |  |   |        |     |         |
| I <sub>S</sub>              | source current                               | T <sub>mb</sub> = 25 °C   | -      | 56  | A       |
| I <sub>SM</sub>             | peak source current                          | pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C   | -      | 226 | A       |
| <b>Avalanche ruggedness</b> |  |   |        |     |         |
| E <sub>DS(AL)S</sub>        | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 56 A; V <sub>sup</sub> ≤ 100 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 5 V; T <sub>j(init)</sub> = 25 °C; unclamped; <a href="#">Fig. 4</a> | [3][4] | -   | 94.1 mJ |

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T<sub>j</sub> and or V<sub>GS</sub>
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.



**Fig. 1. Normalized total power dissipation as a function of mounting base temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$



**Fig. 2. Continuous drain current as a function of mounting base temperature**

$$V_{GS} \geq 5V$$

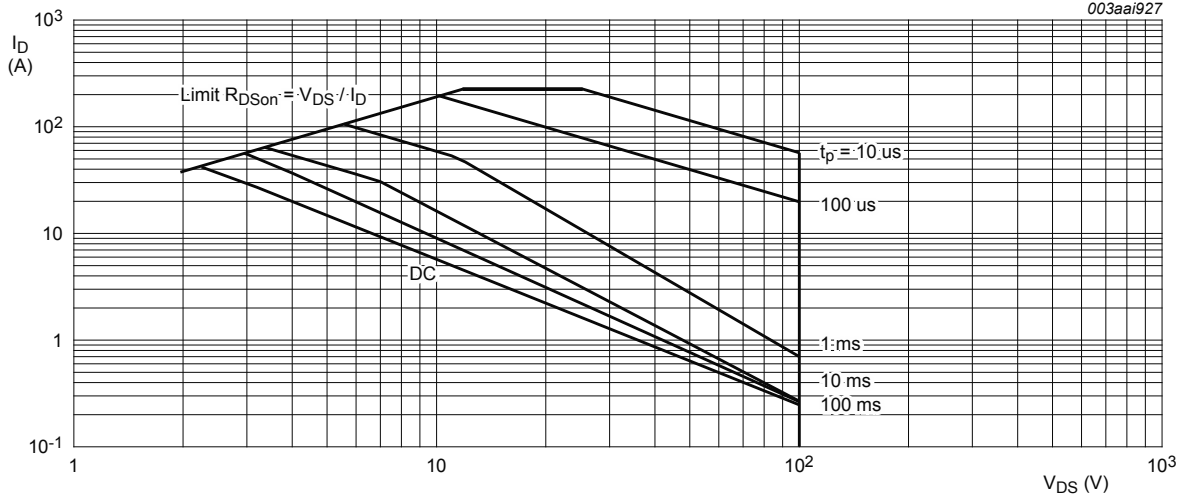


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}\text{C}$ ;  $I_{DM}$  is a single pulse

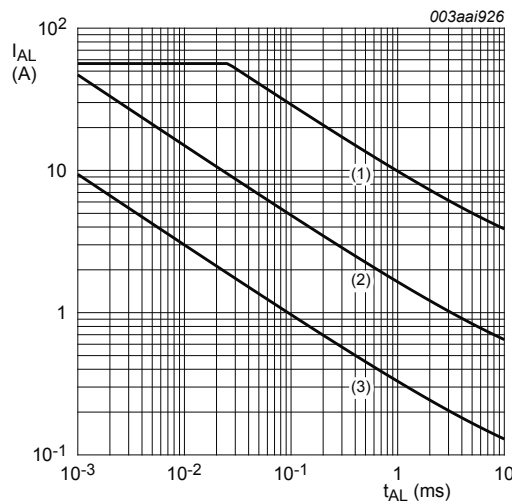


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1)  $T_j(\text{init}) = 25^{\circ}\text{C}$ ; (2)  $T_j(\text{init}) = 150^{\circ}\text{C}$ ; (3) Repetitive Avalanche

## 8. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter   | Conditions | Min | Typ | Max | Unit |
|----------------|---|------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5     | -   | -   | 0.9 | K/W  |

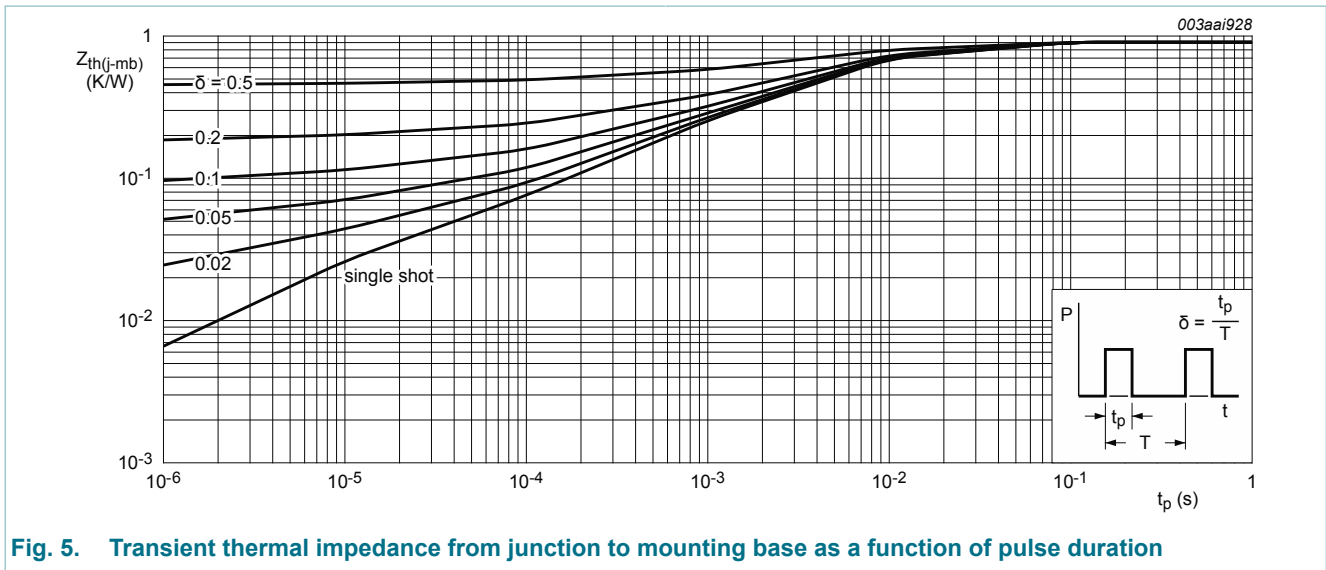


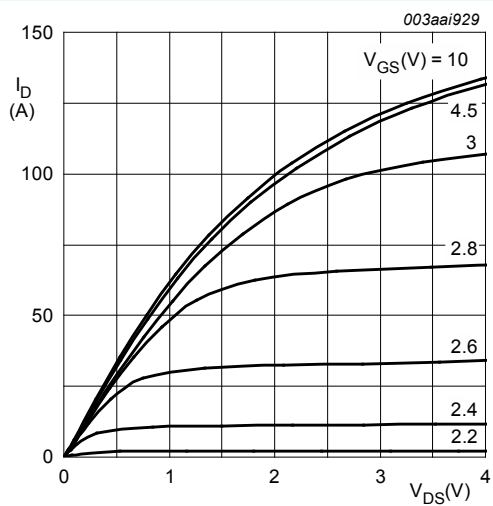
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 9. Characteristics

Table 7. Characteristics

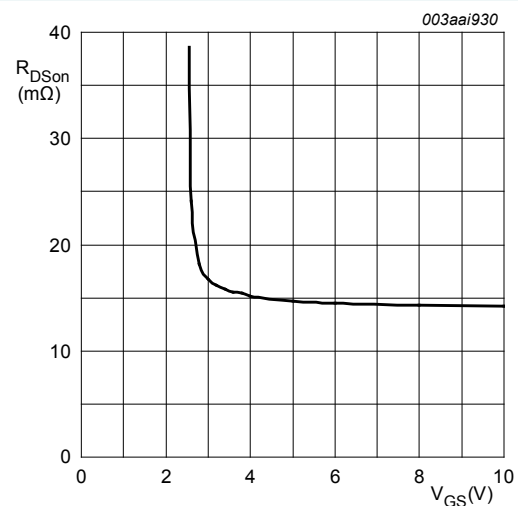
| Symbol                         | Parameter                        | Conditions   | Min | Typ  | Max  | Unit    |
|--------------------------------|----------------------------------|--|-----|------|------|---------|
| <b>Static characteristics</b>  |                                  |  |     |      |      |         |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage   | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$   | 100 | -    | -    | V       |
|                                |                                  | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$  | 90  | -    | -    | V       |
| $V_{GS(th)}$                   | gate-source threshold voltage    | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C$ ; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>                                | 1.4 | 1.7  | 2.1  | V       |
|                                |                                  | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C$ ; <a href="#">Fig. 9</a>   | -   | -    | 2.45 | V       |
|                                |                                  | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C$ ; <a href="#">Fig. 9</a>   | 0.5 | -    | -    | V       |
| $I_{DSS}$                      | drain leakage current            | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$  | -   | 0.04 | 10   | $\mu A$ |
|                                |                                  | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ C$   | -   | -    | 500  | $\mu A$ |
| $I_{GSS}$                      | gate leakage current             | $V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$   | -   | 2    | 100  | nA      |
|                                |                                  | $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$  | -   | 2    | 100  | nA      |
| $R_{DS(on)}$                   | drain-source on-state resistance | $V_{GS} = 5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ C$ ; <a href="#">Fig. 11</a>  | -   | 14.6 | 19   | mΩ      |
|                                |                                  | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ C$ ; <a href="#">Fig. 11</a>   | -   | 14   | 18   | mΩ      |
|                                |                                  | $V_{GS} = 5 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ }^\circ C$ ; <a href="#">Fig. 11</a> ; <a href="#">Fig. 12</a>                       | -   | -    | 52.4 | mΩ      |
| <b>Dynamic characteristics</b> |                                  |  |     |      |      |         |
| $Q_{G(tot)}$                   | total gate charge                | $I_D = 15 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V}; T_j = 25 \text{ }^\circ C$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> | -   | 39   | -    | nC      |
| $Q_{GS}$                       | gate-source charge               |  | -   | 8.5  | -    | nC      |
| $Q_{GD}$                       | gate-drain charge                |  | -   | 14.1 | -    | nC      |

| Symbol                    | Parameter                    | Conditions  | Min | Typ  | Max  | Unit |
|---------------------------|------------------------------|---|-----|------|------|------|
| $C_{iss}$                 | input capacitance            | $V_{DS} = 25\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$                        | -   | 3814 | 5085 | pF   |
| $C_{oss}$                 | output capacitance           | $T_j = 25\text{ °C};$ <a href="#">Fig. 15</a>   | -   | 222  | 266  | pF   |
| $C_{rss}$                 | reverse transfer capacitance |   | -   | 133  | 182  | pF   |
| $t_{d(on)}$               | turn-on delay time           | $V_{DS} = 80\text{ V}; R_L = 5\text{ }Ω; V_{GS} = 5\text{ V};$                        | -   | 18.5 | -    | ns   |
| $t_r$                     | rise time                    | $R_{G(ext)} = 5\text{ }Ω; T_j = 25\text{ °C}$   | -   | 36.8 | -    | ns   |
| $t_{d(off)}$              | turn-off delay time          |   | -   | 59.6 | -    | ns   |
| $t_f$                     | fall time                    |   | -   | 34.3 | -    | ns   |
| <b>Source-drain diode</b> |                              |   |     |      |      |      |
| $V_{SD}$                  | source-drain voltage         | $I_S = 15\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ °C};$ <a href="#">Fig. 16</a> | -   | 0.8  | 1.2  | V    |
| $t_{rr}$                  | reverse recovery time        | $I_S = 15\text{ A}; di_S/dt = -100\text{ A}/μs; V_{GS} = 0\text{ V};$                 | -   | 38   | -    | ns   |
| $Q_r$                     | recovered charge             | $V_{DS} = 25\text{ V}; T_j = 25\text{ °C}$  | -   | 56   | -    | nC   |



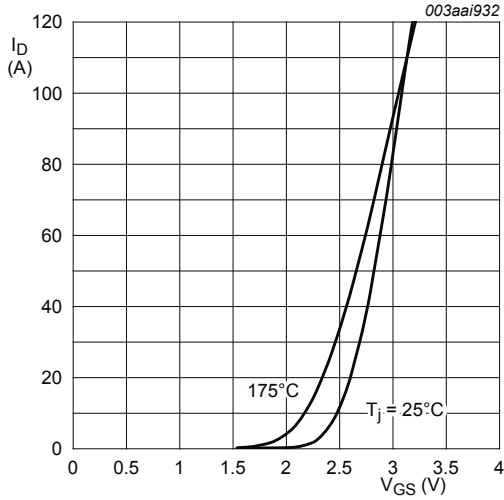
$T_j = 25\text{ °C}; t_p = 300\text{ }μs$

**Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values**



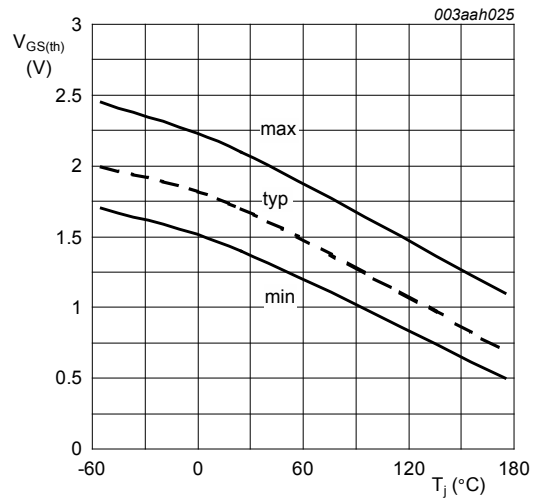
$T_j = 25\text{ °C}; I_D = 15\text{ A}$

**Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**



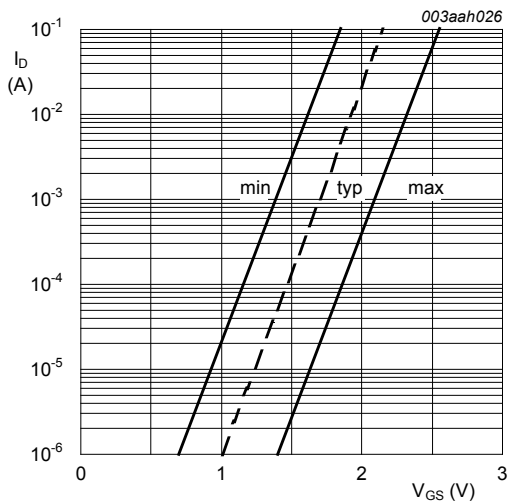
**Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values**

$V_{DS} = 10V$



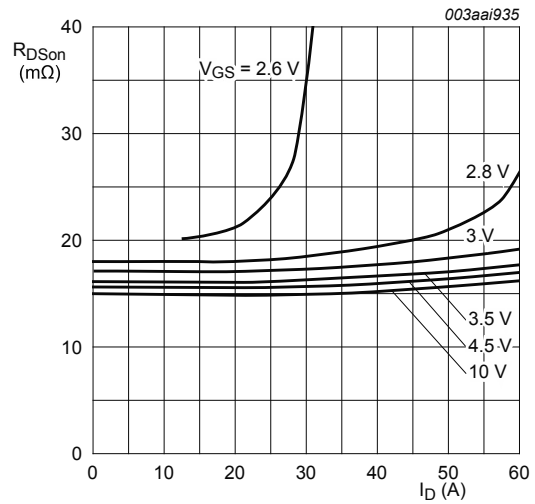
**Fig. 9. Gate-source threshold voltage as a function of junction temperature**

$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$



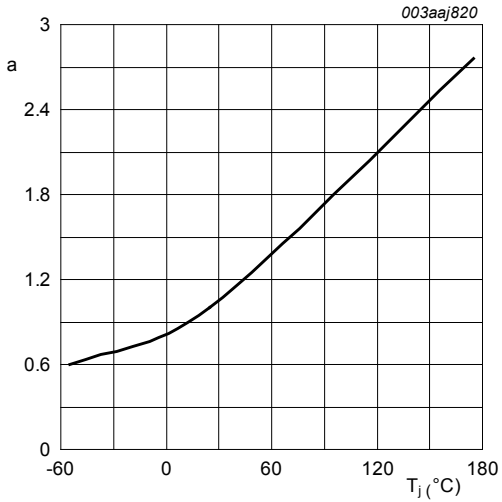
**Fig. 10. Sub-threshold drain current as a function of gate-source voltage**

$T_j = 25^\circ\text{C}; V_{DS} = 5V$



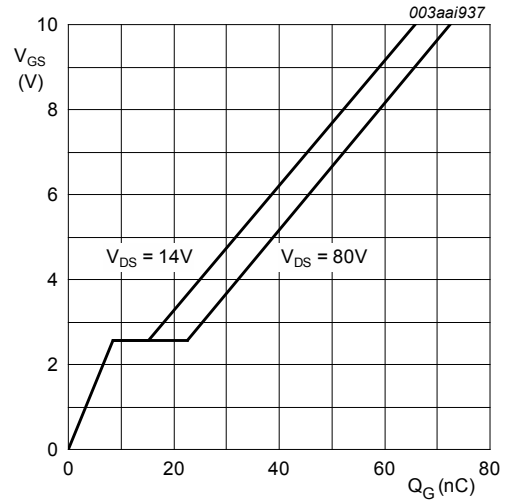
$T_j = 25^\circ\text{C}; t_p = 300 \mu\text{s}$

**Fig. 11. Drain-source on-state resistance as a function of drain current; typical values**



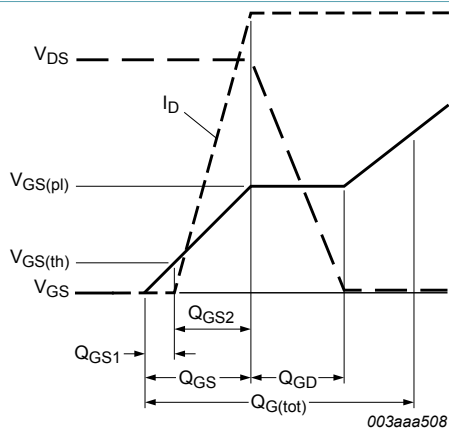
**Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature**

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

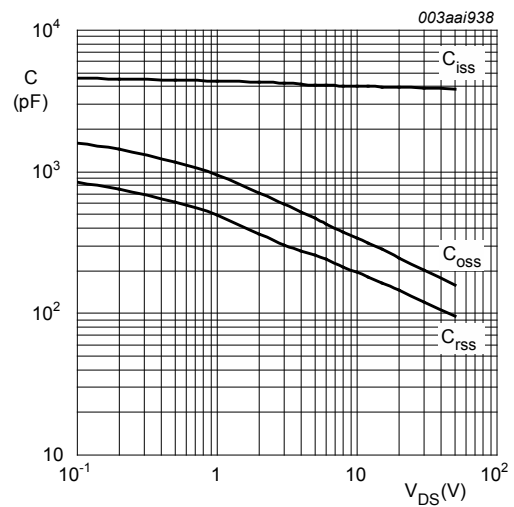


**Fig. 13. Gate-source voltage as a function of gate charge; typical values**

$T_j = 25^{\circ}\text{C}; I_D = 15\text{A}$



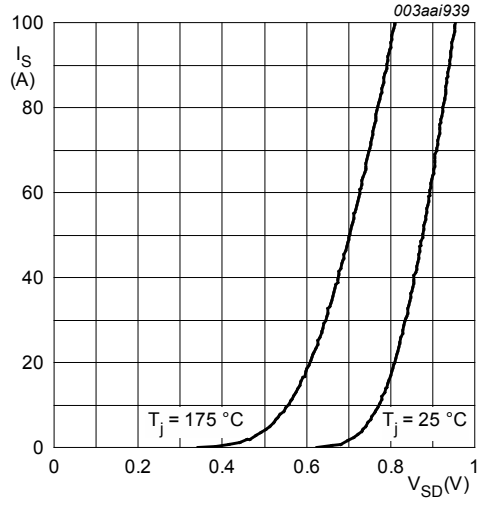
**Fig. 14. Gate charge waveform definitions**



**Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

$V_{GS} = 0\text{V}; f = 1\text{MHz}$



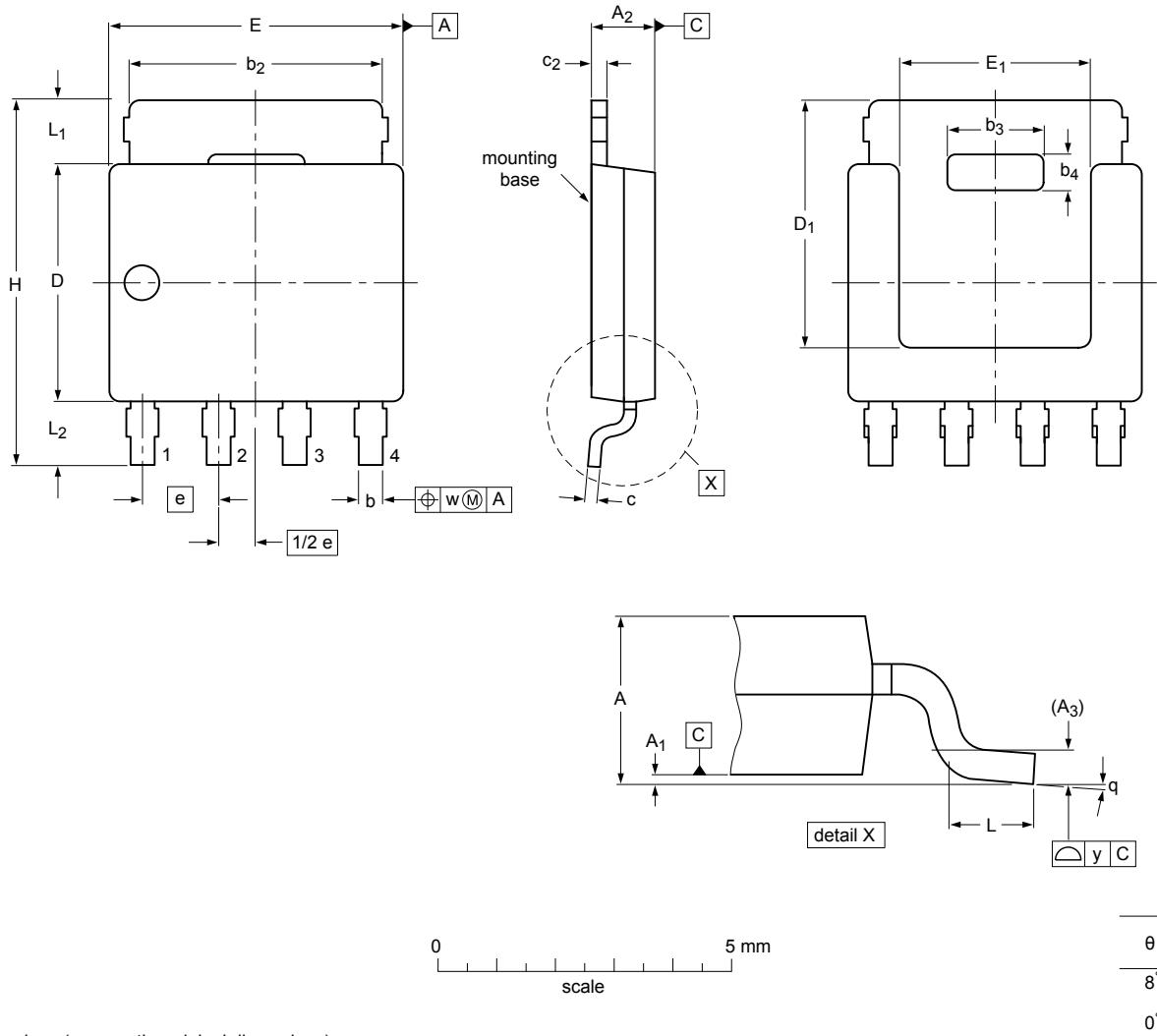


**Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values**

$$V_{GS} = 0V$$

### 10. Package outline

Plastic single-ended surface-mounted package (LPAK56; Power-SO8); 4 leads SOT669



Dimensions (mm are the original dimensions)

| Unit <sup>(1)</sup> | A    | A <sub>1</sub> | A <sub>2</sub> | A <sub>3</sub> | b    | b <sub>2</sub> | b <sub>3</sub> | b <sub>4</sub> | c    | c <sub>2</sub> | D <sup>(1)</sup> | D <sub>1</sub> <sup>(1)</sup> | E <sup>(1)</sup> | E <sub>1</sub> <sup>(1)</sup> | e    | H   | L    | L <sub>1</sub> | L <sub>2</sub> | w    | y   |
|---------------------|------|----------------|----------------|----------------|------|----------------|----------------|----------------|------|----------------|------------------|-------------------------------|------------------|-------------------------------|------|-----|------|----------------|----------------|------|-----|
| max                 | 1.20 | 0.15           | 1.10           |                | 0.50 | 4.41           | 2.2            | 0.9            | 0.25 | 0.30           | 4.10             | 4.20                          | 5.0              | 3.3                           |      | 6.2 | 0.85 | 1.3            | 1.3            |      |     |
| nom                 |      |                |                | 0.25           |      |                |                |                |      |                |                  |                               |                  |                               | 1.27 |     |      |                |                | 0.25 | 0.1 |
| min                 | 1.01 | 0.00           | 0.95           |                | 0.35 | 3.62           | 2.0            | 0.7            | 0.19 | 0.24           | 3.80             |                               | 4.8              | 3.1                           |      | 5.8 | 0.40 | 0.8            | 0.8            |      |     |

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

sot669\_po

| Outline version | References |        |       |  | European projection | Issue date             |
|-----------------|------------|--------|-------|--|---------------------|------------------------|
|                 | IEC        | JEDEC  | JEITA |  |                     |                        |
| SOT669          |            | MO-235 |       |  |                     | -11-03-25-<br>13-02-27 |

Fig. 17. Package outline LPAK56; Power-SO8 (SOT669)

## 11. Legal information

### 11.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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## 12. Contents

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